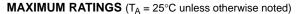
## **General Purpose Transistors**

## **PNP Silicon**

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

#### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$		V
BC856		-65	
BC857		-45	
BC858		-30	
Collector-Base Voltage	V <sub>CBO</sub>		V
BC856		-80	
BC857		-50	
BC858		-30	
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current – Continuous	I <sub>C</sub>	-100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	883	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

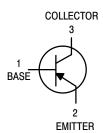
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.



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SC-70/SOT-323 CASE 419 STYLE 3

### **MARKING DIAGRAM**



XX = Specific Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

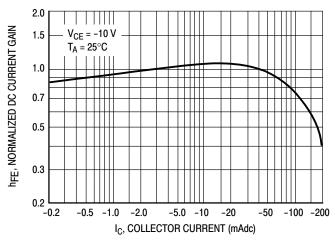
#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	-	•	•
Collector – Emitter Breakdown Voltage BC856 (I <sub>C</sub> = -10 mA) BC857 BC858	V <sub>(BR)</sub> CEO	-65 -45 -30	- - -	- - -	V
	V <sub>(BR)</sub> CES	-80 -50 -30	- - -	- - -	V
Collector – Base Breakdown Voltage BC856 $(I_C = -10 \mu A)$ BC857 BC858	V <sub>(BR)</sub> CBO	-80 -50 -30	- - -	- - -	V
	V <sub>(BR)EBO</sub>	-5.0 -5.0 -5.0	- - -	- - -	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	I <sub>CBO</sub>	_ _	_ _	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain BC856A, BC585A BC856B, BC857B, BC858B BC857C	h <sub>FE</sub>	- - -	90 150 270	- - -	_
$(I_C = -2.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ BC856A, BC858A BC856B, BC857B, BC858B BC857C		125 220 420	180 290 520	250 475 800	
Collector – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>CE(sat)</sub>	_ _	_ _	-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}, I_B = -5.0 \text{ mA}$ )	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C = -2.0$ mA, $V_{CE} = -5.0$ V) ( $I_C = -10$ mA, $V_{CE} = -5.0$ V)	V <sub>BE(on)</sub>	-0.6 -	_ _	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain - Bandwidth Product (I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>ob</sub>	-	-	4.5	pF
Noise Figure ( $I_C = -0.2$ mA, $V_{CE} = -5.0$ Vdc, $R_S = 2.0$ k $\Omega$ , $f = 1.0$ kHz, BW = 200 Hz)	NF	-	_	10	dB

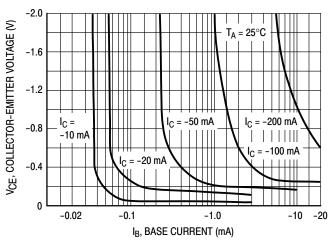
### BC857/BC858



-1.0 -0.9 T<sub>A</sub> = 25°C  $V_{BE(sat)} @ I_C/I_B = 10$ -0.8 V, VOLTAGE (VOLTS) -0.7 $V_{BE(on)}$  @  $V_{CE} = -10 \text{ V}$ -0.6 -0.5 -0.4 -0.3 -0.2  $V_{CE(sat)} @ I_C/I_B = 10$ -0.1 -0.2 -2.0 -0.1 -5.0 -50 -100 IC, COLLECTOR CURRENT (mAdc)

Figure 1. Normalized DC Current Gain

Figure 2. "Saturation" and "On" Voltages



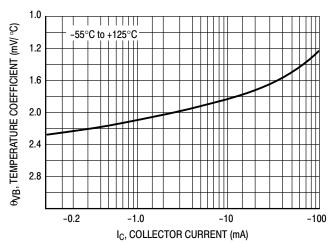
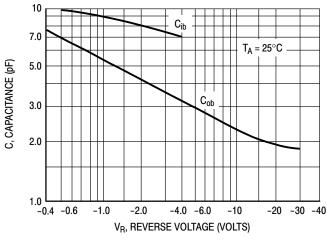


Figure 3. Collector Saturation Region

Figure 4. Base-Emitter Temperature Coefficient



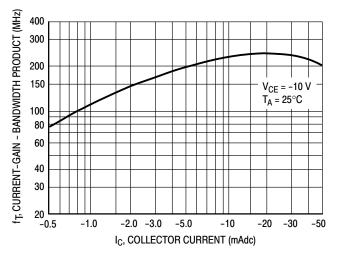


Figure 5. Capacitances

Figure 6. Current-Gain - Bandwidth Product

### **BC856**

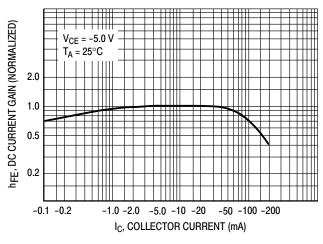


Figure 7. DC Current Gain

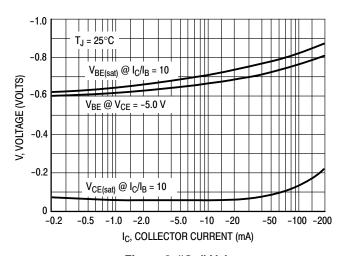


Figure 8. "On" Voltage

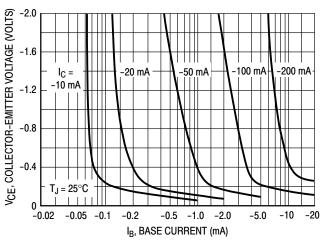


Figure 9. Collector Saturation Region

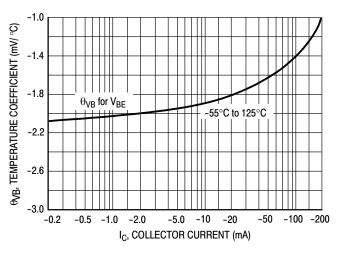


Figure 10. Base-Emitter Temperature Coefficient

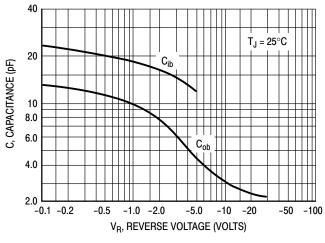


Figure 11. Capacitance

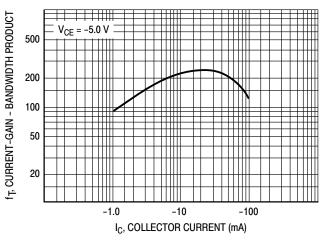


Figure 12. Current-Gain - Bandwidth Product

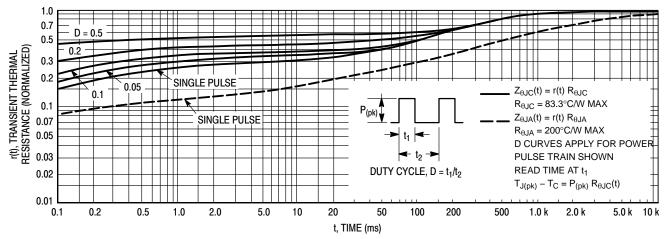


Figure 13. Thermal Response

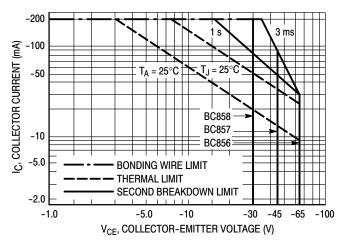


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate  $I_C$ – $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  or  $T_{A}$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

#### **ORDERING INFORMATION**

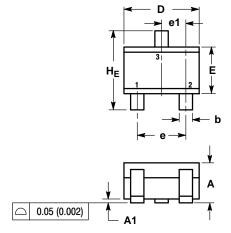
Device	Marking	Package	Shipping <sup>†</sup>	
BC856BWT1G	SC-70/SC		2 000 / Tone & Deel	
SBC856BWT1G*	3B	(Pb-Free)	3,000 / Tape & Reel	
BC857BWT1G	25	SC-70/SOT-323	2 000 / Tana 9 Daal	
SBC857BWT1G*	3F	(Pb-Free)	3,000 / Tape & Reel	
BC857CWT1G	3G	SC-70/SOT-323	2 000 / Tana & Daal	
NSVBC857CWT1G*	36	(Pb-Free)	3,000 / Tape & Reel	
BC858AWT1G	3J	SC-70/SOT-323 (Pb-Free) 3,000 / Tape & Re		
BC858BWT1G	ЗК	SC-70/SOT-323 (Pb-Free)	3,000 / Tape & Reel	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

### PACKAGE DIMENSIONS

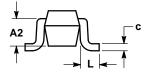
SC-70 (SOT-323) CASE 419-04 **ISSUE N** 





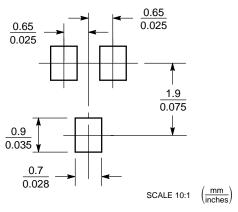
- 11. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



STYLE 3 BASE **EMITTER** 

### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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